

SPEC SHEET (FOR REFERENCE)	SHEET No.	Rev.	Page.
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TYPE: 6PC1606N1T * *	
CHIP SIZE	0.36 * 0.36mm
WAFER SIZE	6 inch

Maximum Ratings (Ta=25°C)

Characteristics	Symbol	Ratings	Unit
Drain-Source voltage	V _{DSS}	50	V
Gate-Source voltage	V _{GSS}	±8	V

WAFER PROBING SPEC (Ta=25°C)

No	MODE	LIMIT				CONDITIONS
		MIN.	Typ	MAX.	UNIT	
1	IGSS			±1	uA	VGS=±8V, VDS=0V
2	IDSS			10	uA	VDS=52V, VGS=0V
3	BVDSS	52			V	ID=100uA, VGS=0V
4	V _{th}	0.65		1.05	V	ID=250uA, VGS=VDS
5	RDS(on)		3.5	5	Ω	VGS=4.0V, ID=100mA
6	Yfs	180			mS	VDS=10V, ID=100mA

※Built in ZD between Gate and Source

PHENITEC SEMICONDUCTOR Corp.